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## **HSM123**

## Silicon Epitaxial Planar Diode for High Speed Switching

# RENESAS

ADE-208-027F (Z)

Rev.6 Nov. 2002

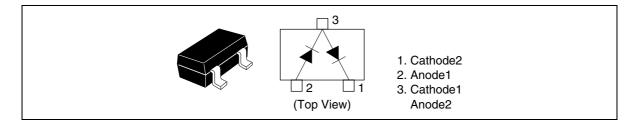
#### Features

- Low capacitance, proof against high voltage.
- Fast recovery time.
- MPAK package is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HSM123	A9	МРАК

### **Pin Arrangement**



## **HSM123**

## Absolute Maximum Ratings \*1

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit	
Peak reverse voltage	V <sub>RM</sub>	85	V	
Reverse voltage	V <sub>R</sub>	80	V	
Peak forward current	I <sub>FM</sub>	300	mA	
Non-Repetitive peak forward surge current	I <sub>FSM</sub> * <sup>2</sup>	4	А	
Average forward current	I <sub>o</sub>	100	mA	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes: 1. Per one device.

2. Within 1  $\mu$ s forward surge current.

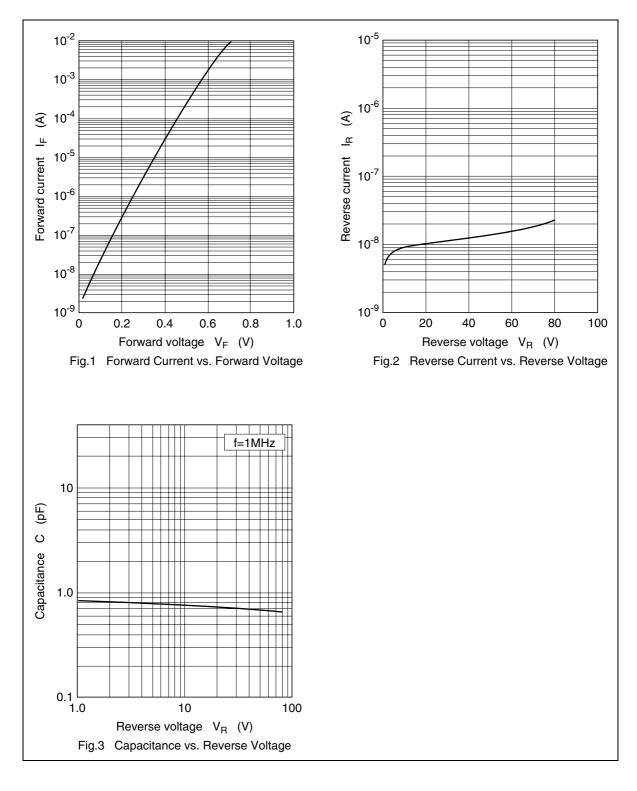
### **Electrical Characteristics \***

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F1</sub>	_	0.70	1.0	V	I <sub>F</sub> = 10 mA
	V <sub>F2</sub>	_	0.79	1.0	_	I <sub>F</sub> = 50 mA
	V <sub>F3</sub>	_	0.85	1.2		I <sub>F</sub> = 100 mA
Reverse current	I <sub>R</sub>	_	_	0.1	μA	V <sub>R</sub> = 80 V
Capacitance	С	_	1.0	4.0	pF	$V_{_{\mathrm{R}}} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$
Reverse recovery time	t <sub>rr</sub>	_		3.0	ns	$I_{_{F}}$ = 10 mA, $V_{_{R}}$ = 6 V, $R_{_{L}}$ = 50 $\Omega$

Note: Per one device.

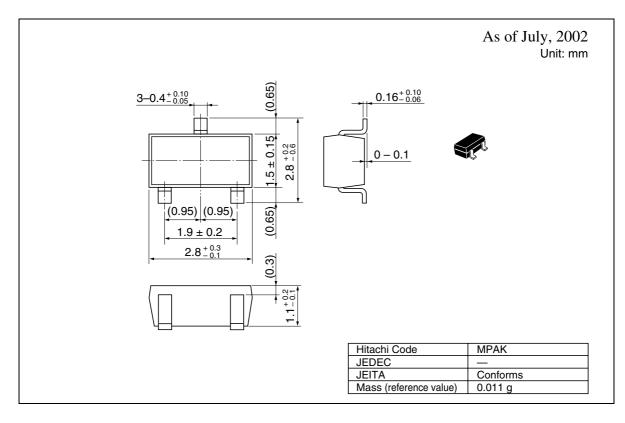
### **Main Characteristic**



RENESAS

## **HSM123**

## **Package Dimensions**





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